

BT138-600

4Q Triac

2 August 2012

Product data sheet

1. Product profile

1.1 General description

Planar passivated four quadrant triac in a SOT78 (TO-220AB) plastic package intended for use in applications requiring high bidirectional transient and blocking voltage capability and high thermal cycling performance. Typical applications include motor control, industrial and domestic lighting, heating and static switching.

1.2 Features and benefits

- High blocking voltage capability
- Less sensitive gate for improved noise immunity
- Planar passivated for voltage ruggedness and reliability
- Triggering in all four quadrants

1.3 Applications

- General purpose motor control
- General purpose switching

1.4 Quick reference data

Table 1. Quick reference data

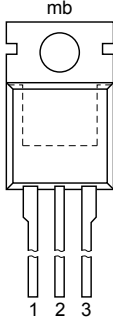
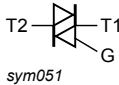
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	-	600	V
I_{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(\text{init})} = 25\text{ }^{\circ}\text{C}$; $t_p = 20\text{ ms}$; Fig. 4 ; Fig. 5	-	-	95	A
T_j	junction temperature		-	-	125	$^{\circ}\text{C}$
$I_{T(\text{RMS})}$	RMS on-state current	full sine wave; $T_{mb} \leq 99\text{ }^{\circ}\text{C}$; Fig. 1 ; Fig. 2 ; Fig. 3	-	-	12	A
Static characteristics						
I_{GT}	gate trigger current	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G+; $T_j = 25\text{ }^{\circ}\text{C}$; Fig. 7	-	5	35	mA
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G-; $T_j = 25\text{ }^{\circ}\text{C}$; Fig. 7	-	8	35	mA
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2- G-; $T_j = 25\text{ }^{\circ}\text{C}$; Fig. 7	-	10	35	mA



Symbol	Parameter	Conditions	Min	Typ	Max	Unit
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2- G+; $T_j = 25\text{ }^\circ\text{C}$; Fig. 7	-	22	70	mA
Dynamic characteristics						
dV_D/dt	rate of rise of off-state voltage	$V_{DM} = 402\text{ V}$; $T_j = 125\text{ }^\circ\text{C}$; ($V_{DM} = 67\%$ of V_{DRM}); exponential waveform; gate open circuit	100	250	-	V/ μs

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	 <p>TO-220AB (SOT78)</p>	 <p>sym051</p>
2	T2	main terminal 2		
3	G	gate		
mb	T2	mounting base; main terminal 2		

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BT138-600	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78
BT138-600/DG	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	600	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{mb} \leq 99\text{ }^\circ\text{C}$; Fig. 1 ; Fig. 2 ; Fig. 3	-	12	A

Symbol	Parameter	Conditions	Min	Max	Unit
I_{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25\text{ }^{\circ}\text{C}$; $t_p = 20\text{ ms}$; Fig. 4; Fig. 5	-	95	A
		full sine wave; $T_{j(init)} = 25\text{ }^{\circ}\text{C}$; $t_p = 16.7\text{ ms}$	-	105	A
I^2t	I^2t for fusing	$t_p = 10\text{ ms}$; sine-wave pulse	-	45	A^2s
di_T/dt	rate of rise of on-state current	$I_T = 20\text{ A}$; $I_G = 0.2\text{ A}$; $dI_G/dt = 0.2\text{ A}/\mu\text{s}$; T2+ G+	-	50	$\text{A}/\mu\text{s}$
		$I_T = 20\text{ A}$; $I_G = 0.2\text{ A}$; $dI_G/dt = 0.2\text{ A}/\mu\text{s}$; T2+ G-	-	50	$\text{A}/\mu\text{s}$
		$I_T = 20\text{ A}$; $I_G = 0.2\text{ A}$; $dI_G/dt = 0.2\text{ A}/\mu\text{s}$; T2- G-	-	50	$\text{A}/\mu\text{s}$
		$I_T = 20\text{ A}$; $I_G = 0.2\text{ A}$; $dI_G/dt = 0.2\text{ A}/\mu\text{s}$; T2- G+	-	10	$\text{A}/\mu\text{s}$
I_{GM}	peak gate current		-	2	A
P_{GM}	peak gate power		-	5	W
$P_{G(AV)}$	average gate power	over any 20 ms period	-	0.5	W
T_{stg}	storage temperature		-40	150	$^{\circ}\text{C}$
T_j	junction temperature		-	125	$^{\circ}\text{C}$

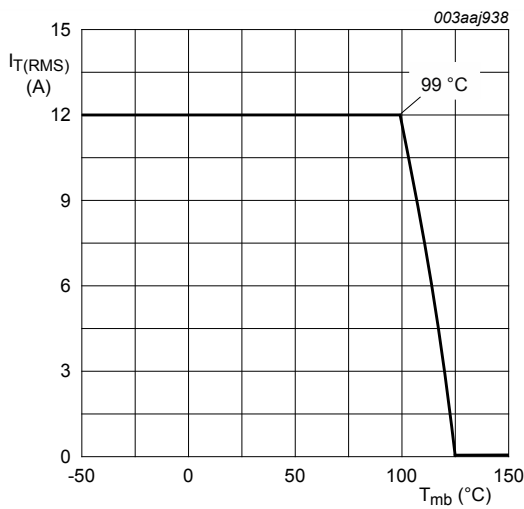
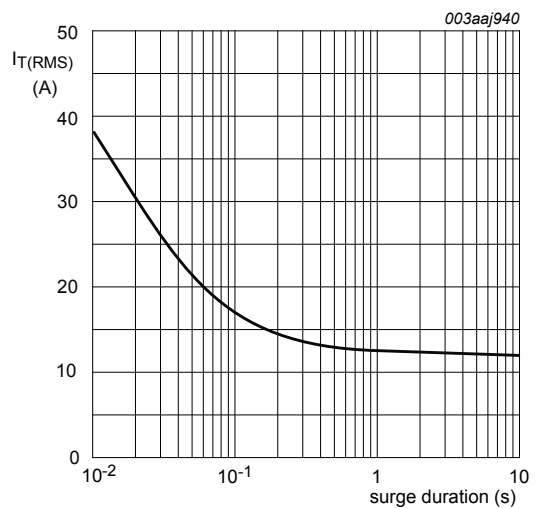


Fig. 1. RMS on-state current as a function of mounting base temperature; maximum values



$f = 50\text{ Hz}$; $T_{mb} = 99\text{ }^{\circ}\text{C}$

Fig. 2. RMS on-state current as a function of surge duration; maximum values

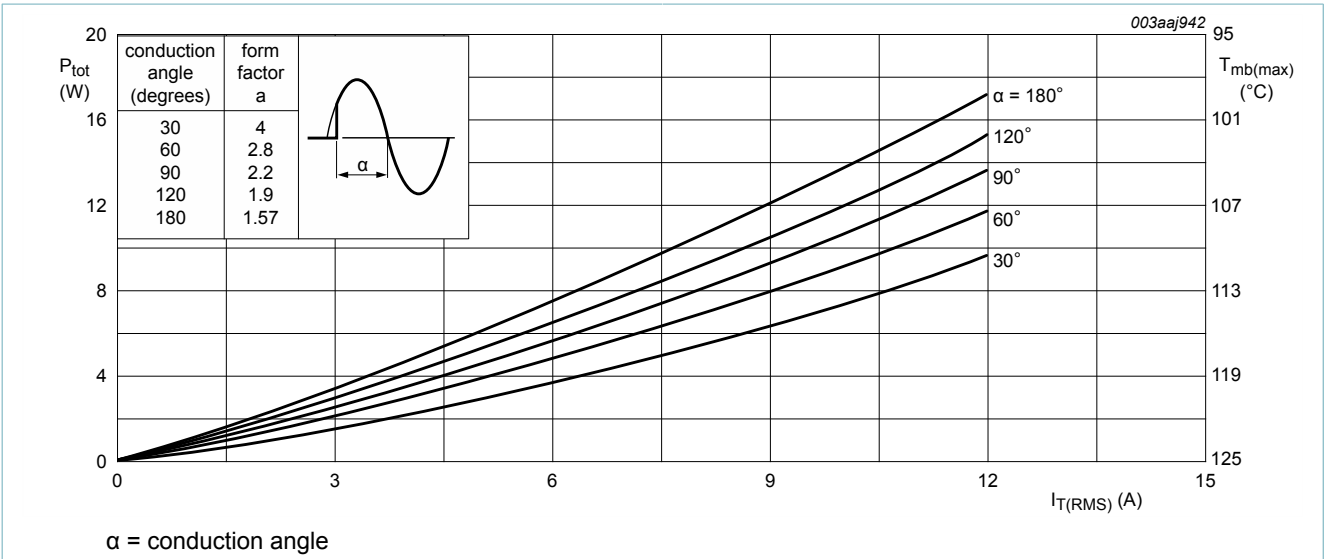


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

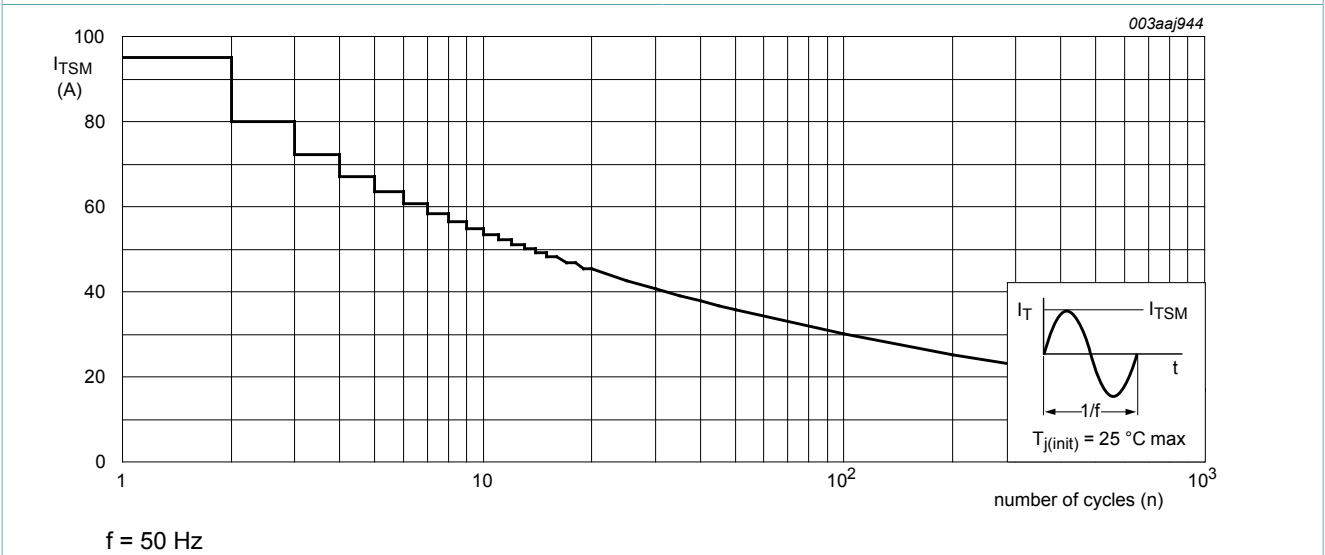
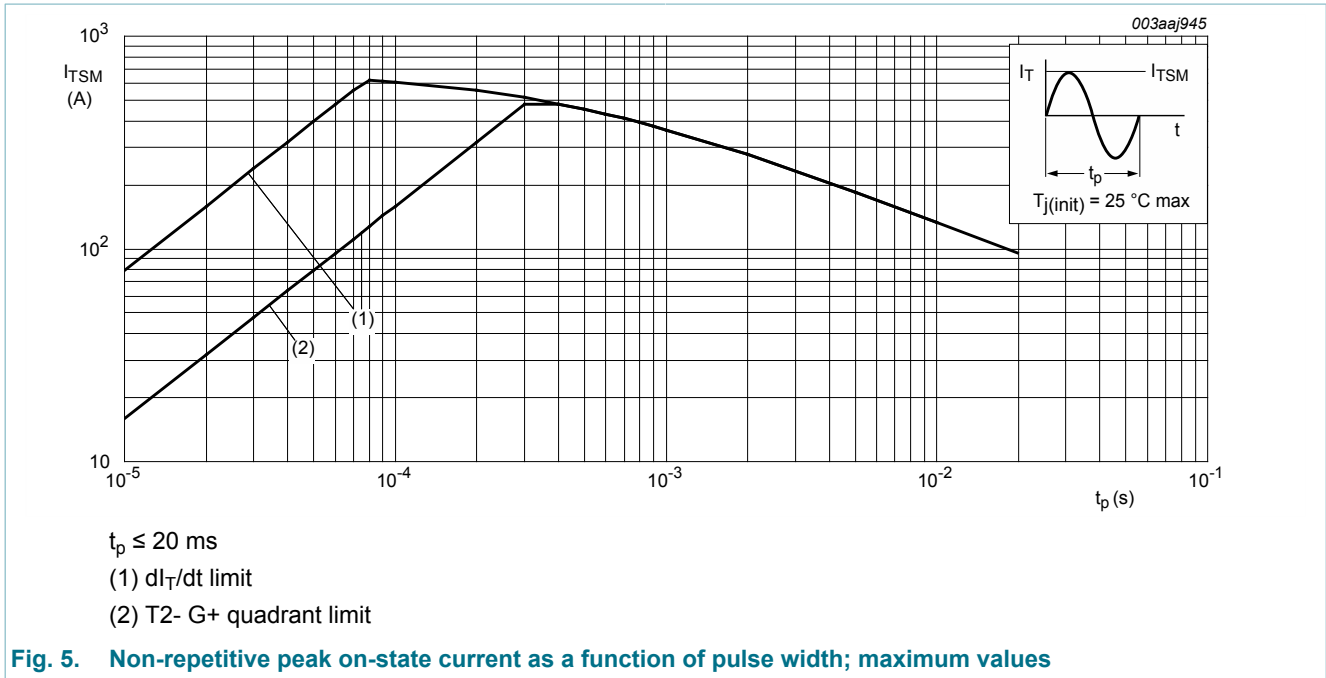


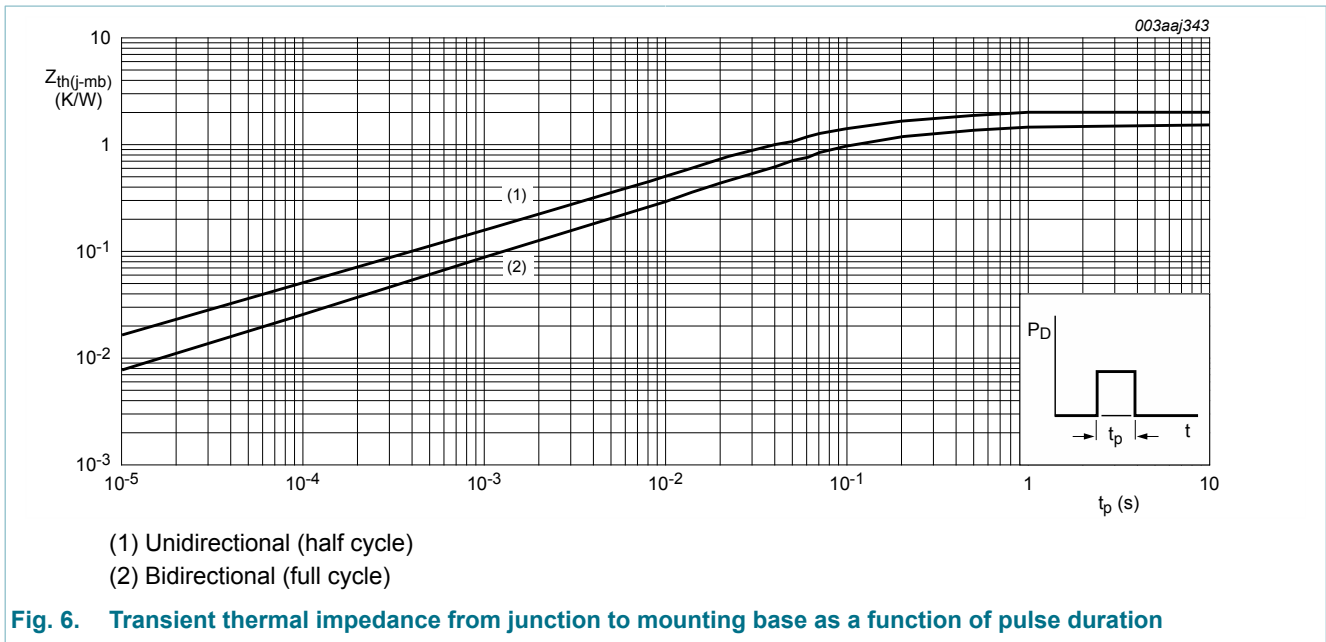
Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	full cycle; Fig. 6	-	-	1.5	K/W
		half cycle; Fig. 6	-	-	2	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	-	60	-	K/W

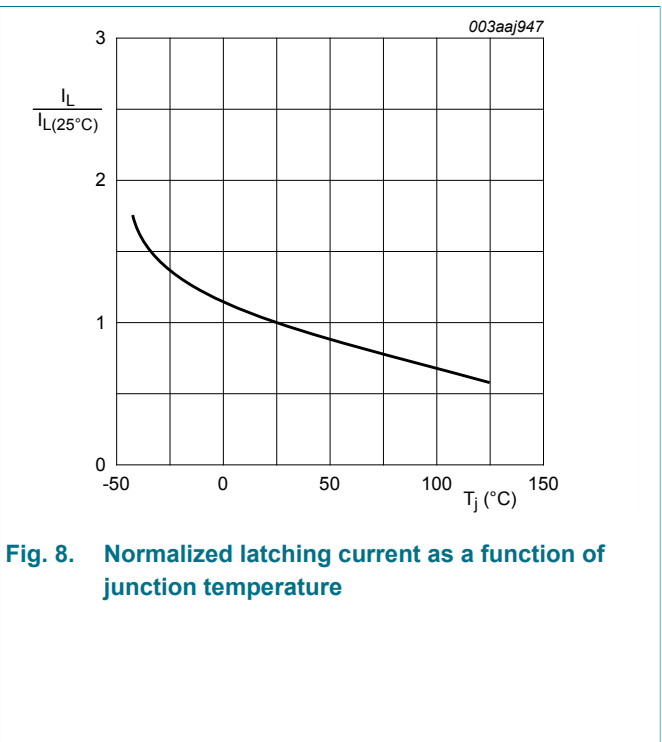
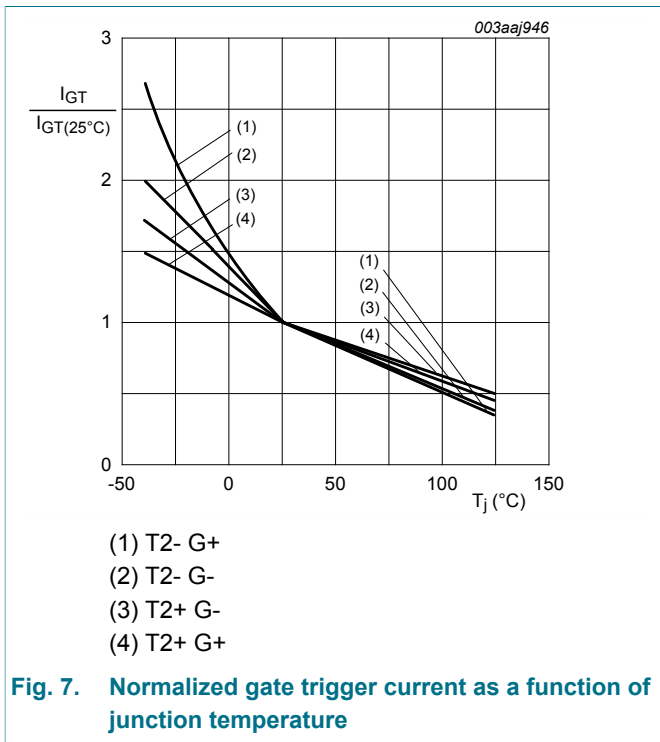


6. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
I_{GT}	gate trigger current	$V_D = 12\text{ V}; I_T = 0.1\text{ A}; T2+ G+;$ $T_j = 25\text{ }^\circ\text{C};$ Fig. 7	-	5	35	mA
		$V_D = 12\text{ V}; I_T = 0.1\text{ A}; T2+ G-;$ $T_j = 25\text{ }^\circ\text{C};$ Fig. 7	-	8	35	mA
		$V_D = 12\text{ V}; I_T = 0.1\text{ A}; T2- G-;$ $T_j = 25\text{ }^\circ\text{C};$ Fig. 7	-	10	35	mA
		$V_D = 12\text{ V}; I_T = 0.1\text{ A}; T2- G+;$ $T_j = 25\text{ }^\circ\text{C};$ Fig. 7	-	22	70	mA
I_L	latching current	$V_D = 12\text{ V}; I_G = 0.1\text{ A}; T2+ G+;$ $T_j = 25\text{ }^\circ\text{C};$ Fig. 8	-	7	40	mA
		$V_D = 12\text{ V}; I_G = 0.1\text{ A}; T2+ G-;$ $T_j = 25\text{ }^\circ\text{C};$ Fig. 8	-	20	60	mA
		$V_D = 12\text{ V}; I_G = 0.1\text{ A}; T2- G-;$ $T_j = 25\text{ }^\circ\text{C};$ Fig. 8	-	8	40	mA
		$V_D = 12\text{ V}; I_G = 0.1\text{ A}; T2- G+;$ $T_j = 25\text{ }^\circ\text{C};$ Fig. 8	-	10	60	mA
I_H	holding current	$V_D = 12\text{ V}; T_j = 25\text{ }^\circ\text{C};$ Fig. 9	-	6	30	mA
V_T	on-state voltage	$I_T = 15\text{ A}; T_j = 25\text{ }^\circ\text{C};$ Fig. 10	-	1.4	1.65	V

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V _{GT}	gate trigger voltage	V _D = 12 V; I _T = 0.1 A; T _j = 25 °C; Fig. 11	-	0.7	1.5	V
		V _D = 400 V; I _T = 0.1 A; T _j = 125 °C; Fig. 11	0.25	0.4	-	V
I _D	off-state current	V _D = 600 V; T _j = 125 °C	-	0.1	0.5	mA
Dynamic characteristics						
dV _D /dt	rate of rise of off-state voltage	V _{DM} = 402 V; T _j = 125 °C; (V _{DM} = 67% of V _{DRM}); exponential waveform; gate open circuit	100	250	-	V/μs
t _{gt}	gate-controlled turn-on time	I _{TM} = 16 A; V _D = 600 V; I _G = 0.1 A; dI _G /dt = 5 A/μs	-	2	-	μs



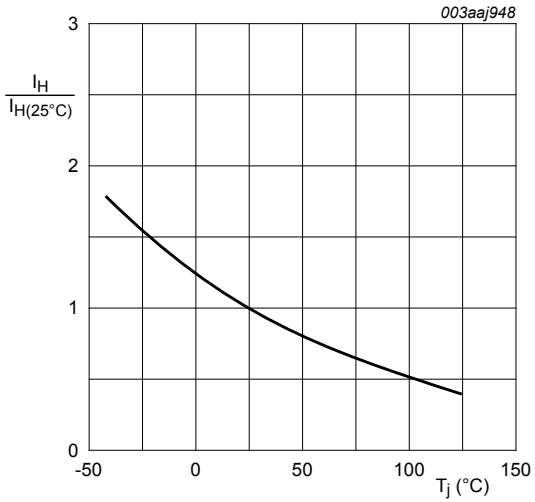
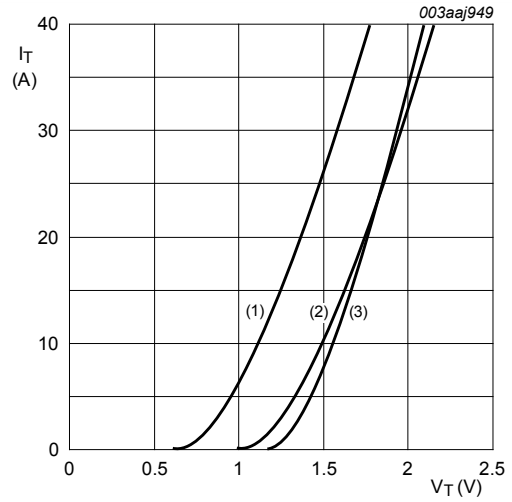


Fig. 9. Normalized holding current as a function of junction temperature



$V_o = 1.175 \text{ V}$; $R_s = 0.0316 \ \Omega$

(1) $T_j = 125 \text{ }^\circ\text{C}$; typical values

(2) $T_j = 125 \text{ }^\circ\text{C}$; maximum values

(3) $T_j = 25 \text{ }^\circ\text{C}$; maximum values

Fig. 10. On-state current as a function of on-state voltage

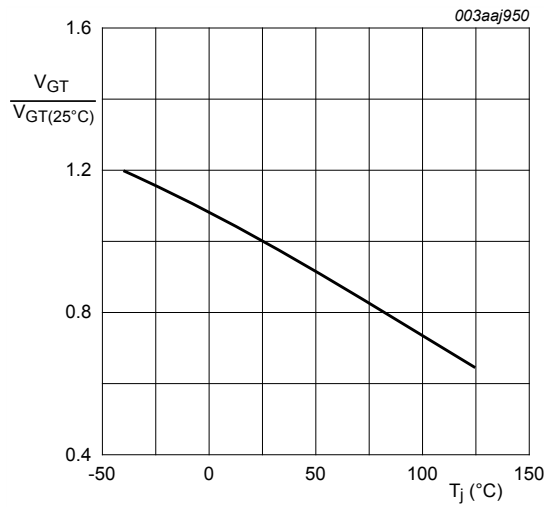
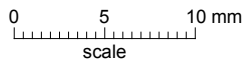
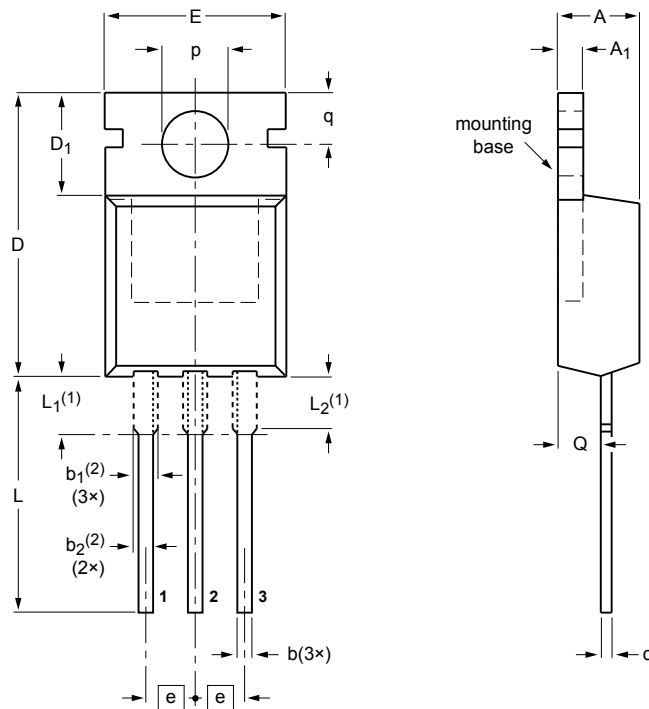


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

7. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB

SOT78



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁	b	b ₁ (2)	b ₂ (2)	c	D	D ₁	E	e	L	L ₁ (1)	L ₂ (1) max.	p	q	Q
mm	4.7 4.1	1.40 1.25	0.9 0.6	1.6 1.0	1.3 1.0	0.7 0.4	16.0 15.2	6.6 5.9	10.3 9.7	2.54	15.0 12.8	3.30 2.79	3.0	3.8 3.5	3.0 2.7	2.6 2.2

Notes

- 1. Lead shoulder designs may vary.
- 2. Dimension includes excess dambar.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT78		3-lead TO-220AB	SC-46			08-04-23 08-06-13

Fig. 12. TO-220AB (SOT78)

8. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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